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Understanding Embedded - Microprocessors

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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	600MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (1)
USB	USB 2.0 (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	Cryptography
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8535eavtakga

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This figure shows the major functional units within the chip.



Figure 1. Chip Block Diagram

1 Pin Assignments and Reset States

NOTE

The naming convention of TSEC1 and TSEC3 is used to allow the splitting voltage rails for the eTSEC blocks and to ease the port of existing PowerQUICC III software

NOTE

The UART_SOUT[0:1] and TEST_SEL pins must be set to a proper state during POR configuration. See Table 1 for more details.



Figure 5. Chip Pin Map Detail C

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
LAD[0:31]	Muxed data / address	K22,L21,L22,K23,K24, L24,L25,K25,L28,L27, K28,K27,J28,H28,H27, G27,G26,F28,F26,F25, E28,E27,E26,F24,E24, C26,G24,E23,G23,F22, G22,G21	I/O	BV _{DD}	5,9,29
LDP[0:3]	Data parity	K26,G28,B27,E25	I/O	BV _{DD}	29
LA[27]	Burst address	L19	0	BV _{DD}	5,9,29
LA[28:31]	Port address	K16,K17,H17,G17	0	BV _{DD}	5,7,9,29
LCS[0:4]	Chip selects	K18,G19,H19,H20,G16	0	BV _{DD}	29
LCS5/DMA_DREQ2	Chips selects / DMA Request	H16	I/O	BV _{DD}	1,29
LCS6/DMA_DACK2	Chips selects / DMA Ack	J16	0	BV _{DD}	1,29
LCS7/DMA_DDONE2	Chips selects / DMA Done	L18	0	BV _{DD}	1,29
LWE0/LBS0/LFWE	Write enable / Byte select	J22	0	BV _{DD}	5,9,29
LWE[1:3]/LBS[1:3]	Write enable / Byte select	H22,H23,H21	0	BV _{DD}	5,9,29
LBCTL	Buffer control	J25	0	BV _{DD}	5,8,9,29
LALE	Address latch enable	J26	0	BV _{DD}	5,8,9,29
LGPL0/LFCLE	UPM general purpose line 0 / FLash command latch enable	J20	0	BV _{DD}	5,9,29
LGPL1/LFALE	UPM general purpose line 1 / Flash address latch enable	K20	0	BV _{DD}	5,9,29
LGPL2/LOE/LFRE	UPM general purpose line 2 / Output enable/Flash read enable	G20	0	BV _{DD}	5,8,9,29
LGPL3/LFWP	UPM general purpose line 3 / Flash write protect	H18	0	BV _{DD}	5,9,29
LGPL4/ <mark>LGTA</mark> /LUPWAIT /LPBSE/LFRB	UPM general purpose line 4 / Target Ack/Wait/SDRAM parity byte select/Flash Ready-busy	L20	I/O	BV _{DD}	29, 35
LGPL5	UPM general purpose line 5 / Amux	К19	0	BV _{DD}	5,9,29
LCLK[0:2]	Local bus clock	H24,J24,H25	0	BV _{DD}	29
LSYNC_IN	Synchronization	D27	I	BV _{DD}	29
LSYNC_OUT	Local bus DLL	D28	0	BV _{DD}	29
	D	MA			
DMA_DACK[0:1] /GPIO[10:11]	DMA Acknowledge	AD6,AE10	0	OV _{DD}	_

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TX_CLK	Transmit clock In	U10	I	TV _{DD}	_
TSEC3_GTX_CLK	Transmit clock Out	U5	0	TV _{DD}	—
TSEC3_CRS	Carrier sense	T10	I/O	TV _{DD}	17
TSEC3_COL	Collision detect	Т9	I	TV _{DD}	_
TSEC3_RXD[7:0]	Receive data	U12,U13,U6,V6,V1,U3, U2,V3	I	TV _{DD}	—
TSEC3_RX_DV	Receive data valid	V2	I	TV _{DD}	_
TSEC3_RX_ER	Receive data error	T4	I	TV _{DD}	
TSEC3_RX_CLK	Receive clock	U1	ļ	TV _{DD}	
	IEEI	E 1588			
TSEC_1588_CLK	Clock In	W9	I	LV _{DD}	29
TSEC_1588_TRIG_IN[0:1]	Trigger In	W8,W7	I	LV _{DD}	29
TSEC_1588_TRIG_OUT[0:1]	Trigger Out	U11,W10	0	LV _{DD}	5,9,29
TSEC_1588_CLK_OUT	Clock Out	V10	0	LV _{DD}	5,9,29
TSEC_1588_PULSE_OUT1	Pulse Out1	V11	0	LV _{DD}	5,9,29
TSEC_1588_PULSE_OUT2	Pulse Out2	T11	0	LV _{DD}	5,9,29
	eS	DHC			•
SDHC_CMD	Command line	AH10	I/O	OV _{DD}	29
SDHC_CD/GPIO[4]	Card detection	AH11	I	OV _{DD}	_
SDHC_DAT[0:3]	Data line	AG12,AH12,AH13, AG11	I/O	OV _{DD}	29
SDHC_DAT[4:7] / SPI_CS[0:3]	8-bit MMC Data line / SPI chip select	AE8,AC10,AF9,AA10	I/O	OV _{DD}	29
SDHC_CLK	SD/MMC/SDIO clock	AG13	I/O	OV _{DD}	29
SDHC_WP/GPIO[5]	Card write protection	AG10	I	OV _{DD}	1, 32
	е	SPI			L
SPI_MOSI	Master Out Slave In	AF8	I/O	OV _{DD}	29
SPI_MISO	Master In Slave Out	AD9	I	OV _{DD}	29
SPI_CLK	eSPI clock	AD8	I/O	OV _{DD}	29
SPI_CS[0:3] / SDHC_DAT[4:7]	eSPI chip select / SDHC 8-bit MMC data	AE8,AC10,AF9,AA10	I/O	OV _{DD}	29
	DL	JART	-	-	
UART_CTS[0:1]	Clear to send	AE11,Y12	I	OV _{DD}	29
UART_RTS[0:1]	Ready to send	AB12,AD12	0	OV _{DD}	29
UART_SIN[0:1]	Receive data	AC12,AF12	I	OV _{DD}	29

Table 1. Pinout Listing (continued)

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes	
25. When a PCI block is disabled, either the POR config pin that selects between internal and external arbiter must be pulled down to select external arbiter if there is any other PCI device connected on the PCI bus, or leave the address pins as "No Connect" or terminated through 2–10 KΩ pull-up resistors with the default of internal arbiter if the address pins are not connected to any other PCI device. The PCI block will drive the address pins if it is configured to be the PCI arbiter—through POR config pins—irrespective of whether it is disabled via the DEVDISR register or not. It may cause contention if there is any other PCI device.						
26. When operating in DDR2 m mode) precision 1% resistor, mode) precision 1% resistor mode) or 40- Ω (half-strength mode) or 40- Ω (half-strength mode) or 40- Ω (half-strength mode) or 40- Ω	ode, connect MDIC[0] to ground and connect MDIC[1] to GVDD . When operating in DDR3 mod n mode) precision 1% resistor, a n mode) precision 1% resistor.	d through an 18.2-Ω (full-st b through an 18.2-Ω (full-st de, connect MDIC[0] to gro and connect MDIC[1] to G These pins are used for a	trength mode rength mode ound through VDD through utomatic calil) or 36.4-Ω (ha) or 36.4-Ω (ha an 20-Ω (full- n an 20-Ω (full- pration of the	alf-strength alf-strength -strength I-strength DDR IOs.	
27. Connect to GND through a	pull down 1 k Ω resistor.					
28. It must be the same as \ensuremath{VD}	D_CORE					
29. The output pads are tristate GCR[DEEPSLEEP_Z] =1.	ed and the receivers of pad inp	uts are disabled during th	e Deep Sleer	o state when		
30. DDRCLK input is only requ configured to run in synchr recommended to tie it off to <i>III Integrated Host Process</i> PLL Ratio" and Table 4-10 operation in asynchronous	ired when the DDR controller is onous mode via POR setting c GND when DDR controller is ru or Family Reference Manual, 7 "DDR Complex Clock PLL Rati and synchronous modes.	s running in asynchronous fg_ddr_pll[0:2]=111, the E unning in synchronous mo Table 4-3 in section 4.2.2 ' io" for more detailed descr	s mode. Whe DRCLK inpu de. See the <i>I</i> 'Clock Signal ription regard	n the DDR co it is not requir <i>MPC8536E Po</i> is", section 4.4 ling DDR cont	ntroller is ed. It is <i>werQUICC</i> 4.3.2 "DDR troller	
31 EC GTX CLK125 is a 125	-MHz input clock shared among	n all eTSEC ports in the fo	llowing mode	s GMILTRI	RGMII and	

- 31. EC_GTX_CLK125 is a 125-MHz input clock shared among all eTSEC ports in the following modes: GMII, TBI, RGMII and RTBI. If none of the eTSEC ports is operating in these modes, the EC_GTX_CLK125 input can be tied off to GND.
- 32. SDHC_WP is active low signal, which follows SDHC Host controller specification. However, it is reversed polarity for SD/MMC card specification.
- 33. Must connect to XGND.
- 34. Must connect to X2GND
- 35. For systems which boot from Local Bus(GPCM)-controlled NOR flash or (FCM) controlled NAND flash, a pullup on LGPL4 is required.

2 Electrical Characteristics

2.1 **Overall DC Electrical Characteristics**

This section covers the ratings, conditions, and other characteristics.

2.6 DDR2 and DDR3 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the chip. Note that DDR2 SDRAM is $GV_{DD}(type) = 1.8 \text{ V}$ and DDR3 SDRAM is $GV_{DD}(type) = 1.5 \text{ V}$.

2.6.1 DDR2 and DDR3 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the chip when interfacing to DDR2 SDRAM.

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV _{DD}	1.7	1.9	V	1
I/O reference voltage	MV _{REF}	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} - 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.125	GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.125	V	—
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.420 V)	I _{ОН}	-13.4	—	mA	—
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	—	mA	—

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the chip. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF} This rail should track variations in the DC level of MV_{REF}

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

This table provides the recommended operating conditions for the DDR SDRAM controller of the chip when interfacing to DDR3 SDRAM.

Table 13. DDR3 SDRAM Interface DC Electrica	al Characteristics for GV _{DD} (typ) = 1.5 V
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Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV _{DD}	1.425	1.575	V	1
I/O reference voltage	MV _{REF} n	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
Input high voltage	V _{IH}	MV _{REF} <i>n</i> + 0.100	GV _{DD}	V	—
Input low voltage	V _{IL}	GND	MV _{REF} <i>n</i> – 0.100	V	—
Output leakage current	I _{OZ}	-50	50	μA	3

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. $MV_{REF}n$ is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±1% of the DC value.

3. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

2.6.2.2 DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications

This table contains the output AC timing targets for the DDR2 and DDR3 SDRAM interface.

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions with GVDD of 1.8 V \pm 5% for DDR2 or 1.5 V \pm 5% for DDR3.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t _{MCK}	3.0	5	ns	2
ADDR/CMD output setup with respect to MCK	t _{DDKHAS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
ADDR/CMD output hold with respect to MCK	t _{DDKHAX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
MCS[n] output setup with respect to MCK	t _{DDKHCS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
MCS[n] output hold with respect to MCK	t _{DDKHCX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
MCK to MDQS Skew	t _{DDKHMH}			ns	4
<= 667 MHz		-0.6	0.6		7
MDQ/MECC/MDM output setup with respect to MDQS	t _{DDKHDS,} t _{DDKLDS}			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQ/MECC/MDM output hold with respect to MDQS	^t DDKHDX, ^t DDKLDX			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQS preamble start	t _{DDKHMP}			ns	6

The IEEE 1588 AC timing specifications are in the following table.

Table 43. eTSEC IEEE 1588 AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol	Min	Тур	Max	Unit	Note
TSEC_1588_CLK clock period	t _{T1588CLK}	3.8	_	T _{TX_CLK} *7	ns	1
TSEC_1588_CLK duty cycle	t _{T1588} CLKH /t _{T1588} CLK	40	50	60	%	_
TSEC_1588_CLK peak-to-peak jitter	t _{T1588CLKINJ}	—	_	250	ps	_
Rise time eTSEC_1588_CLK (20%-80%)	t _{T1588CLKINR}	1.0	_	2.0	ns	_
Fall time eTSEC_1588_CLK (80%-20%)	t _{T1588CLKINF}	1.0	—	2.0	ns	
TSEC_1588_CLK_OUT clock period	t _{T1588CLKOUT}	2*t _{T1588CLK}	_	_	ns	_
TSEC_1588_CLK_OUT duty cycle	t _{T1588} CLKOTH /t _{T1588} CLKOUT	30	50	70	%	_
TSEC_1588_PULSE_OUT	t _{T1588OV}	0.5	_	3.0	ns	_
TSEC_1588_TRIG_IN pulse width	t _{T1588} TRIGH	2*t _{T1588CLK_MAX}	—	—	ns	2

Note:

1. When TMR_CTRL[CKSEL]=00, the external TSEC_1588_CLK input is selected as the 1588 timer reference clock source, with the timing defined in the Table above. The maximum value of t_{T1588CLK} is defined in terms of T_{TX_CLK}, which is the maximum clock cycle period of the equivalent interface speed that the eTSEC1 port is running.

When eTSEC1 is configured to operate in the parallel mode, the T_{TX_CLK} is the maximum clock period of the TSEC1_TX_CLK. When eTSEC1 operates in SGMII mode, the maximum value of $t_{T1588CLK}$ is defined in terms of the recovered clock from SGMII SerDes. For example, for 10/100/1000 Mbps modes, the maximum value of $t_{T1588CLK}$ will be 2800, 280, and 56 ns respectively.

See the MPC8536E PowerQUICC III Integrated Communications Processor Reference Manual for a description of TMR_CTRL registers.

2. It need to be at least two times of clock period of clock selected by TMR_CTRL[CKSEL]. See the *MPC8536E PowerQUICC III Integrated Processor Reference Manual* for a description of TMR_CTRL registers.

2.10 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals EC_MDIO (management data input/output) and EC_MDC (management data clock). The electrical characteristics for GMII, SGMII, RGMII, RMII, TBI and RTBI are specified in Section 2.9, "Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management"

This figures provide the AC test load and signals for the USB, respectively.



Parameter	Configuration	Symbol ¹	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	—	t _{LBKHOX2}	0.9	_	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	—	t _{LBKHOZ1}	_	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	—	t _{LBKHOZ2}	_	2.6	ns	5

Table 53. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC) (continued)

Note:

The symbols used for timing specifications herein follow the pattern of t<sub>(First two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub>

2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.

- 3. All signals are measured from BV_{DD}/2 of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to 0.4 × BV_{DD} of the signal in question for 1.8-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. tLBOTOT is guaranteed with LBCR[AHD] = 0.
- 7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BVDD/2.

This figure provides the AC test load for the local bus.

Figure 38. Local Bus AC Test Load



This figure provides the eSDHC clock input timing diagram.



Figure 43. eSDHC Clock Input Timing Diagram

This figure provides the data and command input/output timing diagram.



VM = Midpoint Voltage (OV_{DD}/2)

Figure 44. eSDHC Data and Command Input/Output Timing Diagram Referenced to Clock

2.14 Programmable Interrupt Controller (PIC)

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

2.15 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the chip.

2.15.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

 Table 57. JTAG DC Electrical Characteristics

Parameter	Symbol ¹	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V

This figure provides the AC test load for TDO and the boundary-scan outputs.



Figure 45. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.



VM = Midpoint Voltage (OV_{DD}/2)

Figure 46. JTAG Clock Input Timing Diagram

This figure provides the $\overline{\text{TRST}}$ timing diagram.



This figure provides the boundary-scan timing diagram.



Figure 48. Boundary-Scan Timing Diagram

2.16 Serial ATA (SATA)

This section describes the DC and AC electrical specifications for the serial ATA (SATA) of the chip. Note that the external cabled applications or long backplane applications (Gen1x & Gen2x) are not supported.

peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.

6. Common Mode Voltage, V_{cm}

The Common Mode Voltage is equal to one half of the sum of the voltages between each conductor of a balanced interchange circuit and ground. In this example, for SerDes output, $V_{cm_out} = V_{SDn_TX} + V_{\overline{SDn_TX}} = (A + B)$ / 2, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred as the DC offset in some occasion.



Figure 57. Differential Voltage Definitions for Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (Current Mode Logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and TD, has a swing that goes between 2.5V and 2.0V. Using these values, the peak-to-peak voltage swing of each signal (TD or TD) is 500 mV p-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 mV and -500 mV, in other words, V_{OD} is 500 mV in one phase and -500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage (V_{DIFFp-p}) is 1000 mV p-p.

2.20.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks for PCI Express are SD1_REF_CLK and, SD1_REF_CLK. The SerDes reference clocks for the SATA and SGMII interfaces are SD2_REF_CLK and, SD2_REF_CLK.

The following sections describe the SerDes reference clock requirements and some application information.

2.20.2.1 SerDes Reference Clock Receiver Characteristics

Figure 58 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for X2V_{DD} are specified in Table 2 and Table 3.
- SerDes Reference Clock Receiver Reference Circuit Structure
 - The SDn_REF_CLK and SDn_REF_CLK are internally AC-coupled differential inputs as shown in Figure 58.
 Each differential clock input (SDn_REF_CLK or SDn_REF_CLK) has a 50-Ω termination to SGND (xcorevss) followed by on-chip AC-coupling.

Symbol	Parameter	Min	Nom	Max	Units	Comments
V _{TX-DE-RATIO}	De- Emphasized Differential Output Voltage (Ratio)	-3.0	-3.5	-4.0	dB	Ratio of the $V_{TX-DIFFp-p}$ of the second and following bits after a transition divided by the $V_{TX-DIFFp-p}$ of the first bit after a transition. See Note 2.
T _{TX-EYE}	Minimum TX Eye Width	0.70	_	_	UI	The maximum Transmitter jitter can be derived as $T_{TX-MAX-JITTER} = 1 - T_{TX-EYE} = 0.3$ UI. See Notes 2 and 3.
T _{TX-EYE-MEDIAN-to-} MAX-JITTER	Maximum time between the jitter median and maximum deviation from the median.	_	_	0.15	UI	Jitter is defined as the measurement variation of the crossing points ($V_{TX-DIFFp-p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2 and 3.
T _{TX-RISE} , T _{TX-FALL}	D+/D- TX Output Rise/Fall Time	0.125	_	_	UI	See Notes 2 and 5
V _{TX-CM-ACp}	RMS AC Peak Common Mode Output Voltage	_	_	20	mV	
VTX-CM-DC-ACTIVE- IDLE-DELTA	Absolute Delta of DC Common Mode Voltage During L0 and Electrical Idle	0		100	mV	$eq:logical_lo$
V _{TX-CM-DC-LINE-DELTA}	Absolute Delta of DC Common Mode between D+ and D-	0	_	25	mV	$\begin{split} & V_{TX-CM-DC-D+} - V_{TX-CM-DC-D-} <= 25 \text{ mV} \\ &V_{TX-CM-DC-D+} = DC_{(avg)} \text{ of } V_{TX-D+} \\ &V_{TX-CM-DC-D-} = DC_{(avg)} \text{ of } V_{TX-D-} \\ &\text{See Note 2.} \end{split}$
V _{TX-IDLE} -DIFFp	Electrical Idle differential Peak Output Voltage	0	_	20	mV	$V_{TX-IDLE-DIFFp} = V_{TX-IDLE-D+} - V_{TX-IDLE-D-} \le 20 \text{ mV}$ See Note 2.
V _{TX-RCV} -DETECT	The amount of voltage change allowed during Receiver Detection	_	_	600	mV	The total amount of voltage change that a transmitter can apply to sense whether a low impedance Receiver is present. See Note 6.
V _{TX-DC-CM}	The TX DC Common Mode Voltage	0	_	3.6	V	The allowed DC Common Mode voltage under any conditions. See Note 6.
I _{TX-SHORT}	TX Short Circuit Current Limit	_	_	90	mA	The total current the Transmitter can provide when shorted to its ground
T _{TX-IDLE-MIN}	Minimum time spent in Electrical Idle	50	_		UI	Minimum time a Transmitter must be in Electrical Idle Utilized by the Receiver to start looking for an Electrical Idle Exit after successfully receiving an Electrical Idle ordered set

Table 71. Differential Transmitter (TX) Output Specifications (continued)

2.21.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 69 is specified using the passive compliance/test measurement load (see Figure 71) in place of any real PCI Express interconnect + RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams will differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit will always be relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).



Figure 69. Minimum Transmitter Timing and Voltage Output Compliance Specifications

2.23.1 Clock Ranges

This table provides the clocking specifications for the processor cores and Table 74 provides the clocking specifications for the memory bus.

	Maximum Processor Core Frequency									
Characteristic	600 MHz		800 MHz		1000 MHz		1250 MHz		Unit	Notes
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	600	600	600	800	600	1000	600	1250	MHz	1, 2
CCB frequency	400	400	400	400	333	400	333	500		
DDR Data Rate	400	400	400	400	400	400	400	500		

Table 73. Processor Core Clocking Specifications

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio," and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.

2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL. This table provides the clocking specifications for the memory bus.

Table 74	. Memory	Bus	Clocking	Specifications
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	Maximum Process	or Core Frequency		Notes	
Characteristic	600, 800, ⁻	1000, 1250	Unit		
	Min	Мах			
DDR Memory bus clock speed	200	250	MHz	1, 2, 3, 4	

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio," and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.

2. The Memory bus clock refers to the chip's memory controllers' MCK[0:5] and MCK[0:5] output clocks, running at half of the DDR data rate.

- 3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
- 4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. See Section 2.23.4, "DDR/DDRCLK PLL Ratio." The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

Please note that the DDR PLL reference clock input, DDRCLK, is only required in asynchronous mode.

The DDRCLKDR configuration register in the Global Utilities block allows the DDR controller to be run in a divided down mode where the DDR bus clock is half the speed of the default configuration. Changing of these defaults must be completed prior to initialization of the DDR controller.

Functional Signals	Reset Configuration Name	Value (Binary)	DDR:DDRCLK Ratio
		000	3:1
TSEC_1588_TRIG_OUT[0:1], TSEC1_1588_CLK_OUT		001	4:1
		010	6:1
	cfg_ddr_pll[0:2]	011	8:1
		100	10:1
		101	12:1
		110	Reserved
		111	Synchronous mode

Table 77. DDR Clock Ratio	able 7	7. DDR	Clock	Ratic
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2.23.5 PCI Clocks

The integrated PCI controller in this chip supports PCI input clock frequency in the range of 33–66 MHz. The PCI input clock can be applied from SYSCLK in synchronous mode or PCI1_CLK in asynchronous mode. For specifications on the PCI1_CLK, refer to the PCI 2.2 Specification.

The use of PCI1_CLK is optional if SYSCLK is in the range of 33–66 MHz. If SYSCLK is outside this range then use of PCI1_CLK is required as a separate PCI clock source, asynchronous with respect to SYSCLK.

The recommended attachment method to the heat sink is illustrated in the following figure. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).



Figure 73. Package Exploded Cross-Sectional View with Several Heat Sink Options

The system board designer can choose between several types of heat sinks to place on the chip. Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Advanced Thermal Solutions, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that will allow the chip to function in various environments.

2.24.3.1 Internal Package Conduction Resistance

For the packaging technology, shown in Table 70, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

This figure depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance)

Figure 74. Package with Heat Sink Mounted to a Printed-Circuit Board

Hardware Design Considerations

The heat sink removes most of the heat from the chip for most applications. Heat generated on the active side of the chip is conducted through the silicon and through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

2.24.3.2 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. The performance of thermal interface materials improves with increased contact pressure. This performance characteristic chart is generally provided by the thermal interface vendors.

3 Hardware Design Considerations

This section provides electrical and thermal design recommendations for successful application of the chip.

3.1 System Clocking

This chip includes seven PLLs:

- The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 2.23.2, "CCB/SYSCLK PLL Ratio."
- The e500 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in Section 2.23.3, "e500 Core PLL Ratio."
- The PCI PLL generates the clocking for the PCI bus
- The local bus PLL generates the clock for the local bus.
- There is a PLL for the SerDes1 block to be used for PCI Express interface
- There is a PLL for the SerDes2 block to be used for SGMII and SATA interfaces.
- The DDR PLL generates the DDR clock from the externally supplied DDRCLK input in asynchronous mode. The frequency ratio between the DDR clock and DDRCLK is described in Section 2.23.4, "DDR/DDRCLK PLL Ratio."

3.2 Power Supply Design and Sequencing

3.2.1 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV_{DD}_PLAT, AV_{DD}_CORE, AV_{DD}_PCI, AV_{DD}_LBIU, and AV_{DD}_SRDS respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages will be derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits per PLL power supply as illustrated in Figure 75, one to each of the AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of 783 FC-PBGA the footprint, without the inductance of vias.



Figure 79. COP Connector Physical Pinout

3.11 Guidelines for High-Speed Interface Termination

3.11.1 SerDes1 Interface Entirely Unused

If the high-speed SerDes interface is not used at all, the unused pin should be terminated as described in this section. However, the SerDes must always have power applied to its supply pins. There are several reserved pins that need to be either left floating or connected to XGND. See SerDes1 in Table 1 for details.

The following pins must be left unconnected (float):

- SD1_TX[7:4]
- SD1_TX[7:4]
- Reserved pins T22, T23

The following pins must be connected to XGND:

- SD1_RX[7:4]
- SD1_RX[7:4]
- SD1_REF_CLK
- SD1 REF CLK

The POR configuration pin cfg_io_ports[0:2] on TSEC3_TXD[6:3] can be used to power down SerDes 1 block for power saving. Note that both SVDD and XVDD must remain powered.

3.11.2 SerDes 1 Interface Partly Unused

If only part of the high speed SerDes interface pins are used, the remaining high-speed serial I/O pins should be terminated as described in this section.

The following pins must be left unconnected (float) if not used:

- SD1_TX[7:4]
- SD1_TX[7:4]
- Reserved pins: T22, T23